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RFMD(R) Receives First GaN Product Purchase Order From Tier-One Wireless Base Station Manufacturer

GREENSBORO, N.C., Nov 12, 2009 (GlobeNewswire via COMTEX News Network) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance semiconductor components, today announced RFMD(R) has received its first purchase order from a tier-one wireless base station original equipment manufacturer (OEM) for a product featuring RFMD's state-of-the-art gallium nitride (GaN) process technology. The purchase order is for RFMD's RFG1M09180 180-watt GaN broadband power transistor (BPT) and is in support of the global expansion of 4G wireless networks.

RFMD's RFG1M09180 BPT supports LTE at 750-800MHz, 3GPP/IS95 at 865-895MHz and multi-carrier GSM at 930-960MHz, thereby enabling cost-effective and energy-efficient support of multi-standard base stations. The RFG1M09180 is part of the RFG1M power device family, which addresses power requirements from 30-watt to 360-watt, offers wider bandwidth than incumbent LDMOS technology and supports wireless communication bands from 0.7GHz to 3.8GHz. The RFG1M power device family also features internal matching and is optimized for high-efficiency techniques, such as Doherty and envelope tracking.

Jeff Shealy, VP and general manager of RFMD's Defense and Power business unit, said, "We are pleased to announce our first GaN purchase order from this tier-one wireless base station OEM. The superior combination of output power, bandwidth and efficiency make RFMD's GaN a compelling process technology and the RFG1M09180 a compelling product for next-generation base station applications."

Bob Van Buskirk, president of RFMD's Multi-Market Products Group (MPG), added, "RFMD is excited to support the development of next-generation base station transmit architectures. Given the superior performance characteristics of our innovative GaN technology, we are enthusiastic about our overall growth opportunities, and we are actively targeting the base station HPA market, which we expect will represent approximately half of the high-power RF market within the next three years."

RFMD's state-of-the-art GaN process technology delivers superior RF power per square millimeter and superior RF conversion efficiency, versus current semiconductor technologies, and RFMD expects its GaN technology will become a disruptive technology across a broad range of commercial and defense markets. In wireless base station applications, RFMD's GaN HPAs deliver industry-leading power performance at significantly reduced energy requirements. This satisfies the increasing focus on "green" technologies by enabling more efficient operation of network equipment and by reducing network-related energy costs.

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance semiconductor components. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

The RF Micro Devices, Inc. logo is available at http://www.globenewswire.com/newsroom/prs/?pkgid=6436

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including risks associated with the recent worldwide economic turmoil and its effect on our business and the business of our suppliers and customers, variability in quarterly operating results, the impact of global macroeconomic and

credit conditions on our business, the rate of growth and development of wireless markets, risks associated with the reduction or elimination of our investments in our wireless systems business, risks that restructuring charges may be greater and that the cost savings and other benefits from our restructurings may be lower than originally anticipated, risks associated with the operation of our wafer fabrication facilities, molecular beam epitaxy facility, assembly facility and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, our ability to reduce costs and improve gross margins by implementing innovative technologies, our ability to bring new products to market, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on a limited number of customers, and dependence on third parties. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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